# Low Power, Low Noise Operational Amplifiers

The MC33178/9 series is a family of high quality monolithic amplifiers employing Bipolar technology with innovative high performance concepts for quality audio and data signal processing applications. This device family incorporates the use of high frequency PNP input transistors to produce amplifiers exhibiting low input offset voltage, noise and distortion. In addition, the amplifier provides high output current drive capability while consuming only  $420~\mu A$  of drain current per amplifier. The NPN output stage used, exhibits no deadband crossover distortion, large output voltage swing, excellent phase and gain margins, low open–loop high frequency output impedance, symmetrical source and sink AC frequency performance.

The MC33178/9 family offers both dual and quad amplifier versions in several package options.

#### **Features**

- 600 Ω Output Drive Capability
- Large Output Voltage Swing
- Low Offset Voltage: 0.15 mV (Mean)
- Low T.C. of Input Offset Voltage: 2.0 μV/°C
- Low Total Harmonic Distortion: 0.0024%
   (@ 1.0 kHz w/600 Ω Load)
- High Gain Bandwidth: 5.0 MHz
- High Slew Rate: 2.0 V/µs
- Dual Supply Operation: ±2.0 V to ±18 V
- ESD Clamps on the Inputs Increase Ruggedness without Affecting Device Performance
- Pb-Free Packages are Available

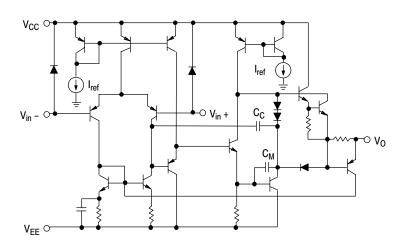


Figure 1. Representative Schematic Diagram (Each Amplifier)



## ON Semiconductor®

http://onsemi.com

DUAL



PDIP-8 P SUFFIX CASE 626



SOIC-8 D SUFFIX CASE 751



Micro8 DM SUFFIX CASE 846A

QUAD



PDIP-14 P SUFFIX CASE 646



SOIC-14 D SUFFIX CASE 751A



TSSOP-14 DTB SUFFIX CASE 948G

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

#### **DEVICE MARKING INFORMATION**

See general marking information in the device marking section on page 4 of this data sheet.

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Supply Voltage (V <sub>CC</sub> to V <sub>EE)</sub>	Vs	+36	V
Input Differential Voltage Range	V <sub>IDR</sub>	Note 1	V
Input Voltage Range	V <sub>IR</sub>	Note 1	V
Output Short Circuit Duration (Note 2)	t <sub>SC</sub>	Indefinite	sec
Maximum Junction Temperature	T <sub>J</sub>	+150	°C
Storage Temperature Range	T <sub>stg</sub>	-60 to +150	°C
Maximum Power Dissipation	P <sub>D</sub>	Note 2	mW
Operating Temperature Range	T <sub>A</sub>	-40 to +85	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

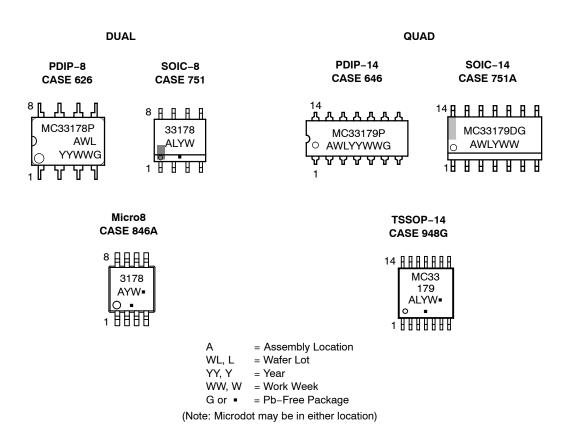
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MC33178D	SOIC-8	
MC33178DG	SOIC-8 (Pb-Free)	98 Units / Rail
MC33178DR2	SOIC-8	
MC33178DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC33178P	PDIP-8	
MC33178PG	PDIP-8 (Pb-Free)	50 Units / Rail
MC33178DMR2	Micro8	
MC33178DMR2G	Micro8 (Pb-Free)	4000 / Tape & Reel
MC33179D	SOIC-14	
MC33179DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC33179DR2	SOIC-14	
MC33179DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC33179P	PDIP-14	
MC33179PG	PDIP-14 (Pb-Free)	25 Units / Rail
MC33179DTBR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

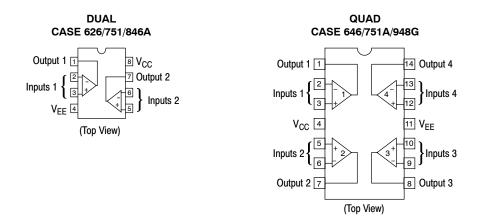
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Either or both input voltages should not exceed V<sub>CC</sub> or V<sub>EE</sub>.
 Power dissipation must be considered to ensure maximum junction temperature (T<sub>J</sub>) is not exceeded. (See power dissipation performance characteristic, Figure 2.)

#### **MARKING DIAGRAMS**



#### **PIN CONNECTIONS**

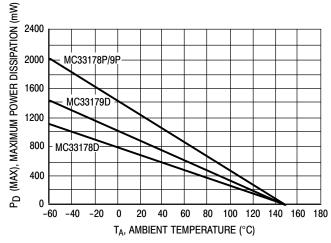


## **DC ELECTRICAL CHARACTERISTICS** ( $V_{CC}$ = +15 V, $V_{EE}$ = -15 V, $T_A$ = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Тур	Max	Unit
Input Offset Voltage (R <sub>S</sub> = 50 $\Omega$ , V <sub>CM</sub> = 0 V, V <sub>O</sub> = 0 V) (V <sub>CC</sub> = +2.5 V, V <sub>EE</sub> = -2.5 V to V <sub>CC</sub> = +15 V, V <sub>EE</sub> = -15 V) $T_A = +25$ °C $T_A = -40$ ° to +85°C	3	V <sub>IO</sub>	- -	0.15 -	3.0 4.0	mV
Average Temperature Coefficient of Input Offset Voltage (R <sub>S</sub> = 50 $\Omega$ , V <sub>CM</sub> = 0 V, V <sub>O</sub> = 0 V) T <sub>A</sub> = -40° to +85°C	3	$\Delta V_{IO}/\Delta T$	_	2.0	_	μV/°C
Input Bias Current ( $V_{CM} = 0 \text{ V}, V_O = 0 \text{ V}$ ) $T_A = +25^{\circ}C$ $T_A = -40^{\circ} \text{ to } +85^{\circ}C$	4, 5	I <sub>IB</sub>	- -	100	500 600	nA
Input Offset Current ( $V_{CM} = 0 \text{ V}, V_O = 0 \text{ V}$ ) $T_A = +25^{\circ}C$ $T_A = -40^{\circ} \text{ to } +85^{\circ}C$		l <sub>IO</sub>	<del>-</del> -	5.0 -	50 60	nA
Common Mode Input Voltage Range $(\Delta V_{IO} = 5.0 \text{ mV}, V_O = 0 \text{ V})$	6	V <sub>ICR</sub>	-13 -	-14 +14	- +13	V
Large Signal Voltage Gain (V $_{O}$ = -10 V to +10 V, R $_{L}$ = 600 $\Omega$ ) $T_{A}$ = +25°C $T_{A}$ = -40° to +85°C	7, 8	A <sub>VOL</sub>	50 25	200	- -	kV/V
Output Voltage Swing ( $V_{ID}$ = ±1.0 V) ( $V_{CC}$ = +15 V, $V_{EE}$ = -15 V) $R_L$ = 300 $\Omega$ $R_L$ = 300 $\Omega$ $R_L$ = 600 $\Omega$ $R_L$ = 600 $\Omega$ $R_L$ = 2.0 k $\Omega$ $R_L$ = 2.0 k $\Omega$ ( $V_{CC}$ = +2.5 V, $V_{EE}$ = -2.5 V) $R_L$ = 600 $\Omega$ $R_L$ = 600 $\Omega$	9, 10, 11	V <sub>O</sub> + V <sub>O</sub> - V <sub>O</sub> + V <sub>O</sub> - V <sub>O</sub> + V <sub>O</sub> -	- +12 - +13 - 1.1	+12 -12 +13.6 -13 +14 -13.8 1.6	- - -12 - -13 - -1.1	V
Common Mode Rejection ( $V_{in} = \pm 13 \text{ V}$ )	12	CMR	80	110	_	dB
Power Supply Rejection $V_{CC}/V_{EE}$ = +15 V/ -15 V, +5.0 V/ -15 V, +15 V/ -5.0 V	13	PSR	80	110	_	dB
Output Short Circuit Current ( $V_{ID}$ = ±1.0 V, Output to Ground) Source ( $V_{CC}$ = 2.5 V to 15 V) Sink ( $V_{EE}$ = -2.5 V to -15 V)	14, 15	I <sub>SC</sub>	+50 -50	+80 -100	- -	mA
Power Supply Current ( $V_O = 0 \text{ V}$ ) ( $V_{CC} = 2.5 \text{ V}$ , $V_{EE} = -2.5 \text{ V}$ to $V_{CC} = +15 \text{ V}$ , $V_{EE} = -15 \text{ V}$ ) MC33178 (Dual) $T_A = +25^{\circ}C$ $T_A = -40^{\circ} \text{ to } +85^{\circ}C$ MC33179 (Quad) $T_A = +25^{\circ}C$ $T_A = -40^{\circ} \text{ to } +85^{\circ}C$	16	I <sub>D</sub>	- - -	- - 1.7	1.4 1.6 2.4 2.6	mA

AC ELECTRICAL CHARACTERISTICS ( $V_{CC}$  = +15 V,  $V_{EE}$  = -15 V,  $T_A$  = 25°C, unless otherwise noted.)

Characteristics	Figure	Symbol	Min	Тур	Max	Unit
Slew Rate $(V_{in} = -10 \text{ V to } +10 \text{ V}, \text{ R}_L = 2.0 \text{ k}\Omega, \text{ C}_L = 100 \text{ pF}, \text{ A}_V = +1.0 \text{ V})$	17, 32	SR	1.2	2.0	-	V/µs
Gain Bandwidth Product (f = 100 kHz)	18	GBW	2.5	5.0	-	MHz
AC Voltage Gain (R <sub>L</sub> = 600 $\Omega$ , V <sub>O</sub> = 0 V, f = 20 kHz)	19, 20	A <sub>VO</sub>	-	50	-	dB
Unity Gain Bandwidth (Open-Loop) (R <sub>L</sub> = 600 $\Omega$ , C <sub>L</sub> = 0 pF)		BW	-	3.0	-	MHz
Gain Margin (R <sub>L</sub> = 600 Ω, C <sub>L</sub> = 0 pF)	21, 23, 24	A <sub>m</sub>	-	15	-	dB
Phase Margin (R <sub>L</sub> = 600 $\Omega$ , C <sub>L</sub> = 0 pF)	22, 23, 24	φm	-	60	-	Deg
Channel Separation (f = 100 Hz to 20 kHz)	25	CS	-	-120	-	dB
Power Bandwidth ( $V_0 = 20 V_{pp}$ , $R_L = 600 \Omega$ , THD $\leq 1.0\%$ )		BW <sub>p</sub>	-	32	-	kHz
Total Harmonic Distortion (R <sub>L</sub> = 600 $\Omega$ ,, V <sub>O</sub> = 2.0 V <sub>pp</sub> , A <sub>V</sub> = +1.0 V) (f = 1.0 kHz) (f = 10 kHz) (f = 20 kHz)	26	THD	- - -	0.0024 0.014 0.024		%
Open Loop Output Impedance (V <sub>O</sub> = 0 V, f = 3.0 MHz, A <sub>V</sub> = 10 V)	27	Z <sub>O</sub>	-	150	-	Ω
Differential Input Resistance (V <sub>CM</sub> = 0 V)		R <sub>in</sub>	-	200	-	kΩ
Differential Input Capacitance (V <sub>CM</sub> = 0 V)		C <sub>in</sub>	-	10	-	pF
Equivalent Input Noise Voltage (Rs = 100 $\Omega$ ,) f = 10 Hz f = 1.0 kHz	28	e <sub>n</sub>	- -	8.0 7.5	- -	nV/√Hz
Equivalent Input Noise Current f = 10 Hz f = 1.0 kHz	29	i <sub>n</sub>	- -	0.33 0.15	-	pA/√Hz





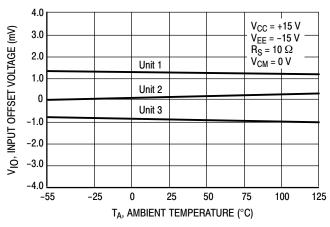


Figure 3. Input Offset Voltage versus Temperature for 3 Typical Units

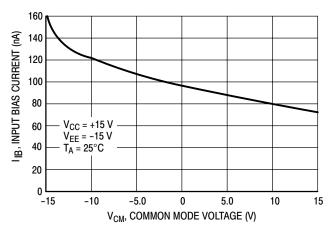


Figure 4. Input Bias Current versus Common Mode Voltage

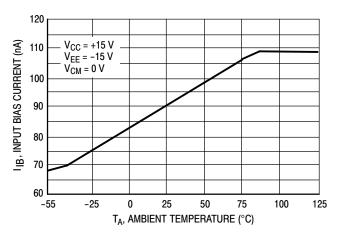


Figure 5. Input Bias Current versus Temperature

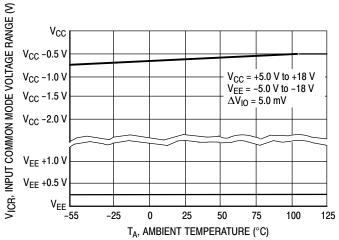


Figure 6. Input Common Mode Voltage Range versus Temperature

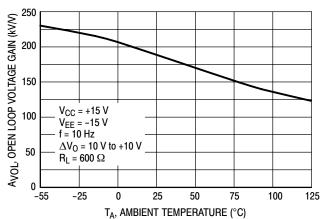


Figure 7. Open Loop Voltage Gain versus Temperature

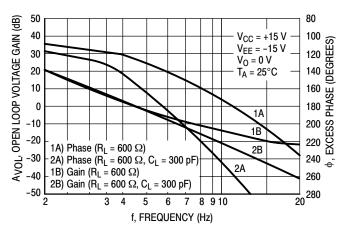


Figure 8. Voltage Gain and Phase versus Frequency

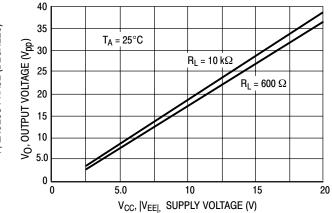


Figure 9. Output Voltage Swing versus Supply Voltage

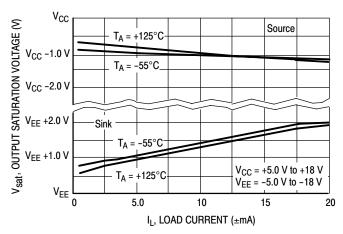


Figure 10. Output Saturation Voltage versus Load Current

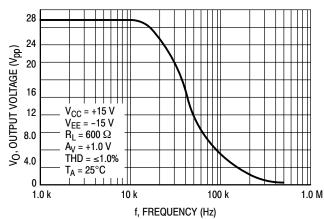


Figure 11. Output Voltage versus Frequency

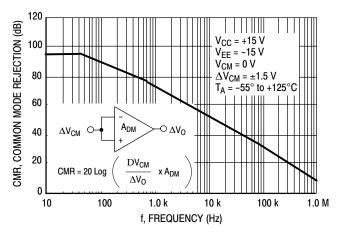


Figure 12. Common Mode Rejection versus Frequency Over Temperature

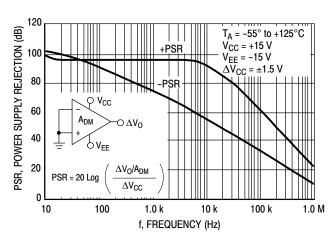


Figure 13. Power Supply Rejection versus Frequency Over Temperature

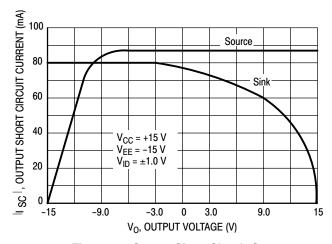


Figure 14. Output Short Circuit Current versus Output Voltage

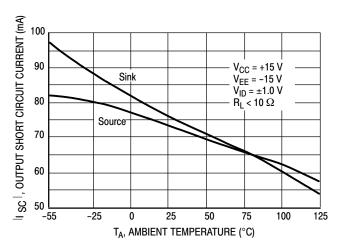


Figure 15. Output Short Circuit Current versus Temperature

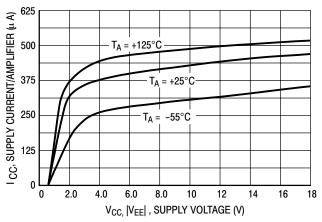


Figure 16. Supply Current versus Supply Voltage with No Load

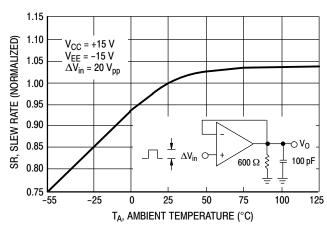


Figure 17. Normalized Slew Rate versus Temperature

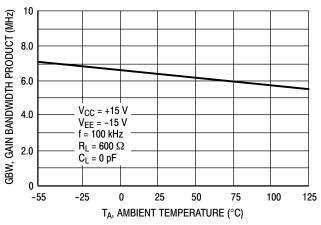


Figure 18. Gain Bandwidth Product versus Temperature

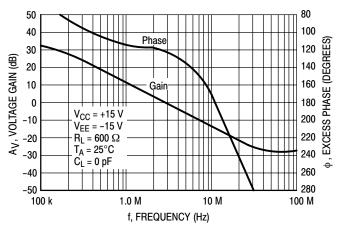


Figure 19. Voltage Gain and Phase versus Frequency

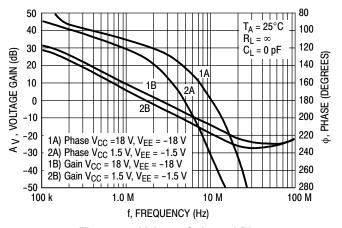


Figure 20. Voltage Gain and Phase versus Frequency

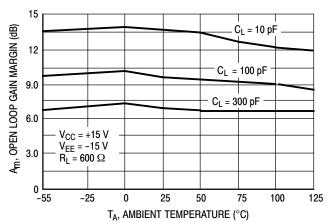


Figure 21. Open Loop Gain Margin versus Temperature

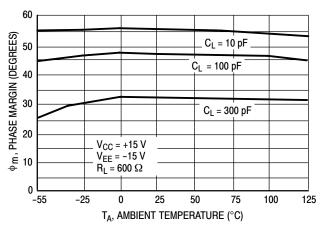


Figure 22. Phase Margin versus Temperature

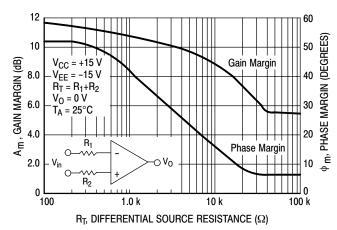


Figure 23. Phase Margin and Gain Margin versus Differential Source Resistance

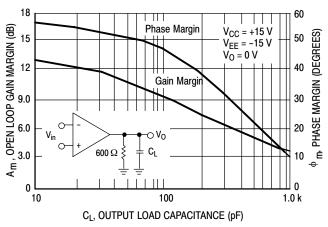


Figure 24. Open Loop Gain Margin and Phase Margin versus Output Load Capacitance

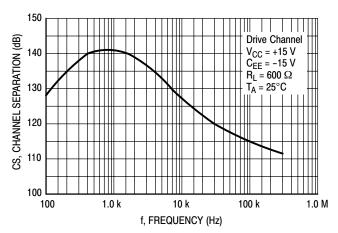


Figure 25. Channel Separation versus Frequency

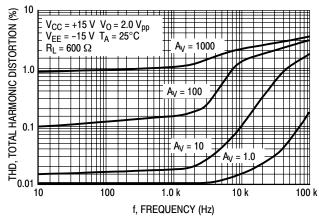


Figure 26. Total Harmonic Distortion versus Frequency

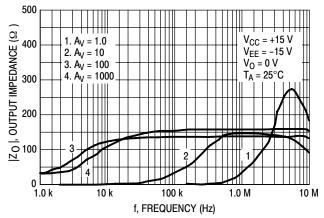


Figure 27. Output Impedance versus Frequency

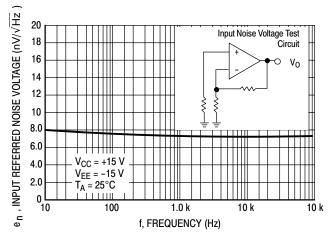


Figure 28. Input Referred Noise Voltage versus Frequency

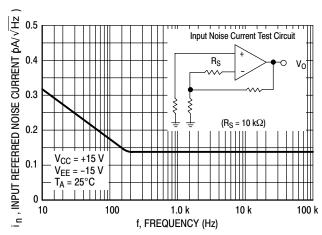


Figure 29. Input Referred Noise Current versus Frequency

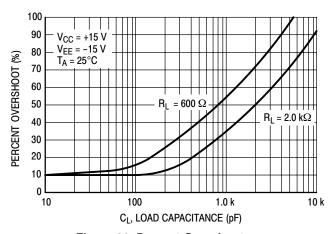


Figure 30. Percent Overshoot versus Load Capacitance

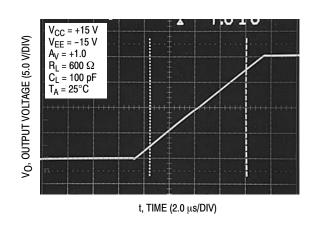


Figure 31. Non-inverting Amplifier Slew Rate

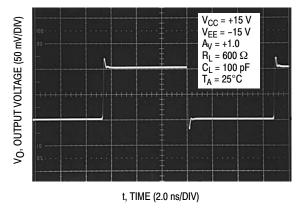


Figure 32. Small Signal Transient Response

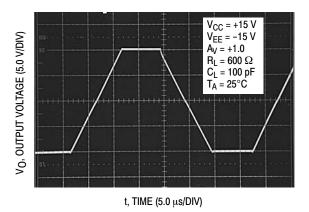


Figure 33. Large Signal Transient Response

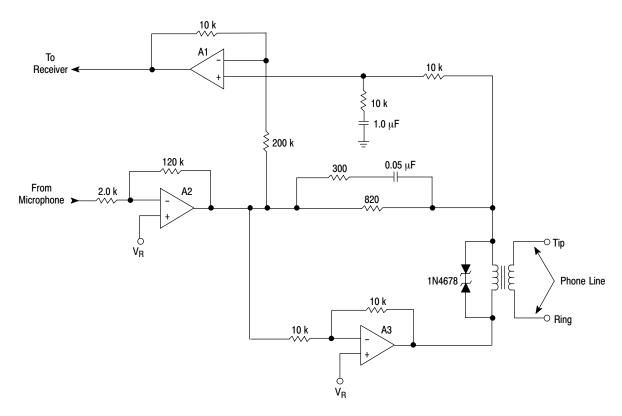


Figure 34. Telephone Line Interface Circuit

#### APPLICATION INFORMATION

This unique device uses a boosted output stage to combine a high output current with a drain current lower than similar bipolar input op amps. Its  $60^\circ$  phase margin and 15 dB gain margin ensure stability with up to 1000 pF of load capacitance (see Figure 24). The ability to drive a minimum  $600~\Omega$  load makes it particularly suitable for telecom applications. Note that in the sample circuit in Figure 34 both A2 and A3 are driving equivalent loads of approximately  $600~\Omega$  .

The low input offset voltage and moderately high slew rate and gain bandwidth product make it attractive for a variety of other applications. For example, although it is not single supply (the common mode input range does not include ground), it is specified at +5.0 V with a typical common mode rejection of 110 dB. This makes it an excellent choice for use with digital circuits. The high common mode rejection, which is stable over temperature, coupled with a low noise figure and low distortion, is an ideal op amp for audio circuits.

The output stage of the op amp is current limited and therefore has a certain amount of protection in the event of a short circuit. However, because of its high current output, it is especially important not to allow the device to exceed the maximum junction temperature, particularly with the MC33179 (quad op amp). Shorting more than one amplifier could easily exceed the junction temperature to the extent of causing permanent damage.

#### Stability

As usual with most high frequency amplifiers, proper lead dress, component placement, and PC board layout should be exercised for optimum frequency performance. For example, long unshielded input or output leads may result in unwanted input/output coupling. In order to preserve the relatively low input capacitance associated with these amplifiers, resistors connected to the inputs should be immediately adjacent to the input pin to minimize additional stray input capacitance. This not only minimizes the input pole frequency for optimum frequency response, but also minimizes extraneous "pick up" at this node. Supplying decoupling with adequate capacitance immediately adjacent to the supply pin is also important, particularly over temperature, since many types of decoupling capacitors exhibit great impedance changes over temperature.

Additional stability problems can be caused by high load capacitances and/or a high source resistance. Simple compensation schemes can be used to alleviate these effects.

If a high source of resistance is used (R1 > 1.0 k $\Omega$ ), a compensation capacitor equal to or greater than the input capacitance of the op amp (10 pF) placed across the feedback resistor (see Figure 35) can be used to neutralize that pole and prevent outer loop oscillation. Since the closed loop transient response will be a function of that capacitance, it is important to choose the optimum value for that capacitor. This can be determined by the following Equation:

$$C_C = (1 + [R1/R2])^2 \times C_L (Z_O/R_2)$$
 (1)

where: Z<sub>O</sub> is the output impedance of the op amp.

For moderately high capacitive loads (500 pF <  $C_L$  < 1500 pF) the addition of a compensation resistor on the order of 20  $\Omega$  between the output and the feedback loop will help to decrease miller loop oscillation (see Figure 36). For high capacitive loads ( $C_L > 1500$  pF), a combined compensation scheme should be used (see Figure 37). Both the compensation resistor and the compensation capacitor affect the transient response and can be calculated for optimum performance. The value of  $C_C$  can be calculated using Equation 1. The Equation to calculate  $R_C$  is as follows:

$$R_C = Z_O \times R_1/R_2$$
 (2)

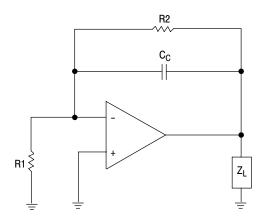


Figure 35. Compensation for High Source Impedance

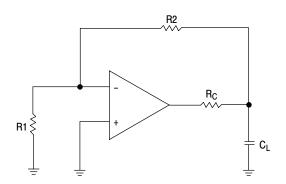


Figure 36. Compensation Circuit for Moderate Capacitive Loads

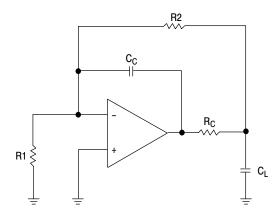


Figure 37. Compensation Circuit for High Capacitive Loads



PDIP-8 CASE 626-05 ISSUE P

**DATE 22 APR 2015** 



**TOP VIEW** 

b2

В



NOTE 5

e/2 NOTE 3 SEATING PLANE C D1 eВ 8X b **END VIEW** |⊕|0.010 M| C| A M| B M NOTE 6 SIDE VIEW

STYLE 1: PIN 1. AC IN 2. DC + IN 3. DC - IN 4. AC IN 5. GROUND 6. OUTPUT 7. AUXILIARY 8. V<sub>CC</sub>

#### NOTES

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
  DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACK-
- AGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
- DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR
- 6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE
- LEADS UNCONSTRAINED.

  DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
- PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52	TYP
С	0.008	0.014	0.20	0.36
D	0.355	0.400	9.02	10.16
D1	0.005		0.13	
E	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54 BSC	
eВ		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

## **GENERIC MARKING DIAGRAM\***



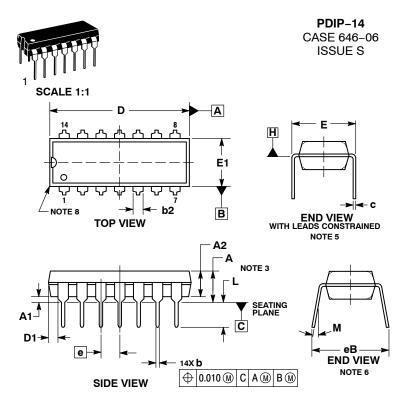
XXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

DOCUMENT NUMBER:	98ASB42420B	Electronic versions are uncontrolled except when accessed directly from the Document Reportant versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	PDIP-8		PAGE 1 OF 1	

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.



**DATE 22 APR 2015** 

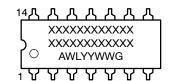
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: INCHES.
  3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
  4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE
- NOT TO EXCEED 0.10 INCH.
  DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
- DIMENSION 6B IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
- DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.

  PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE
- CORNERS).

	INCHES		MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α		0.210		5.33
A1	0.015		0.38	
A2	0.115	0.195	2.92	4.95
b	0.014	0.022	0.35	0.56
b2	0.060	TYP	1.52 TYP	
С	0.008	0.014	0.20	0.36
D	0.735	0.775	18.67	19.69
D1	0.005		0.13	
Е	0.300	0.325	7.62	8.26
E1	0.240	0.280	6.10	7.11
е	0.100	BSC	2.54 BSC	
eВ		0.430		10.92
L	0.115	0.150	2.92	3.81
М		10°		10°

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location

WL = Wafer Lot YY = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

## **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42428B	Electronic versions are uncontrolled except when accessed directly from the Document Reposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	PDIP-14		PAGE 1 OF 2

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

#### PDIP-14 CASE 646-06 ISSUE S

## **DATE 22 APR 2015**

STYLE 1: PIN 1. COLLECTOR 2. BASE 3. EMITTER 4. NO CONNECTION 5. EMITTER 6. BASE 7. COLLECTOR 8. COLLECTOR 9. BASE 10. EMITTER 11. NO CONNECTION 12. EMITTER 13. BASE 14. COLLECTOR	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. DRAIN 2. SOURCE 3. GATE 4. NO CONNECTION 5. GATE 6. SOURCE 7. DRAIN 8. DRAIN 9. SOURCE 10. GATE 11. NO CONNECTION 12. GATE 13. SOURCE 14. DRAIN
STYLE 5: PIN 1. GATE 2. DRAIN 3. SOURCE 4. NO CONNECTION 5. SOURCE 6. DRAIN 7. GATE 8. GATE 9. DRAIN 10. SOURCE 11. NO CONNECTION 12. SOURCE 13. DRAIN 14. GATE	STYLE 6: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 7: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 8: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 9: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE	STYLE 10: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 11: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 12: PIN 1. COMMON CATHODE 2. COMMON ANODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. COMMON ANODE 7. COMMON CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. ANODE/CATHODE 14. ANODE/CATHODE 14. ANODE/CATHODE

DOCUMENT NUMBER:	98ASB42428B	Electronic versions are uncontrolled except when accessed directly from the Document Reposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	PDIP-14		PAGE 2 OF 2

ON Semiconductor and IN are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.





#### SOIC-8 NB CASE 751-07 **ISSUE AK**

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	1.27 BSC		0 BSC
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

## **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year = Work Week W

= Pb-Free Package

XXXXXX XXXXXX AYWW AYWW Ŧ  $\mathbb{H}$ Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α = Year ww = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Reposi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2	

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

#### SOIC-8 NB CASE 751-07 ISSUE AK

## **DATE 16 FEB 2011**

STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE. #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	STYLE 15:  PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW TO GND 2. DASIC OFF 3. DASIC SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

DOCUMENT NUMBER:	98ASB42564B	Electronic versions are uncontrolled except when accessed directly from the Document Repositi Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-8 NB		PAGE 2 OF 2

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

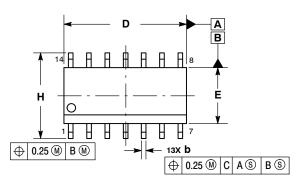




△ 0.10

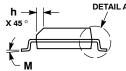
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 









- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  CONTROLLING DIMENSION: MILLIMETERS.
  - DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION
  - SHALL BE 0.13 TOTAL IN EXCESS OF AT
  - MAXIMUM MATERIAL CONDITION.
    DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- 5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27 BSC		0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0 °	7°	0 °	7°

#### **GENERIC MARKING DIAGRAM\***

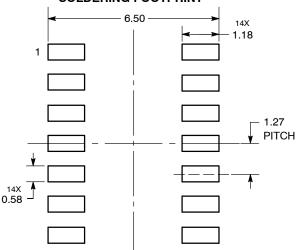


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

## **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

C SEATING PLANE

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED"	
DESCRIPTION:	SOIC-14 NB		PAGE 1 OF 2

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### SOIC-14 CASE 751A-03 ISSUE L

## DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

DOCUMENT NUMBER:	98ASB42565B	Electronic versions are uncontrolled except when accessed directly from the Document Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOIC-14 NB		PAGE 2 OF 2

onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.



#### Micro8 CASE 846A-02 ISSUE K

**DATE 16 JUL 2020** 









#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
- CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION 6 DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION E DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS D AND E ARE DETERMINED AT DATUM F.
- DATUMS A AND B ARE TO BE DETERMINED AT DATUM F.
- A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.



MOUNTING FOOTPRINT

DIM	MILLIMETERS		
ואזמ	MIN.	N□M.	MAX.
Α	-	-	1.10
A1	0.05	0.08	0.15
b	0.25	0.33	0.40
c	0.13	0.18	0.23
D	2.90	3.00	3.10
Ε	2.90	3.00	3.10
е	0.65 BSC		
HE	4.75	4.90	5.05
L	0.40	0.55	0.70

#### **GENERIC MARKING DIAGRAM\***



XXXX = Specific Device Code Α = Assembly Location

Υ = Year W = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. SOURCE	PIN 1. SOURCE 1	PIN 1. N-SOURCE
<ol><li>SOURCE</li></ol>	2. GATE 1	2. N-GATE
<ol><li>SOURCE</li></ol>	3. SOURCE 2	3. P-SOURCE
<ol><li>GATE</li></ol>	4. GATE 2	4. P-GATE
<ol><li>DRAIN</li></ol>	5. DRAIN 2	5. P-DRAIN
<ol><li>DRAIN</li></ol>	6. DRAIN 2	6. P-DRAIN
7. DRAIN	7. DRAIN 1	7. N-DRAIN
8. DRAIN	8. DRAIN 1	8. N-DRAIN

DOCUMENT NUMBER:	ER: 98ASB14087C Electronic versions are uncontrolled except when accessed Printed versions are uncontrolled except when stamped "C		
DESCRIPTION:	MICRO8		PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, Onsemi, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <a href="www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase

#### ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS:** 

 $\textbf{Technical Library:} \ \underline{www.onsemi.com/design/resources/technical-documentation}$ 

onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at

www.onsemi.com/support/sales